



ALPHA & OMEGA
SEMICONDUCTOR

AOT12N60FD/AOB12N60FD/AOTF12N60FD 600V, 12A N-Channel MOSFET

General Description

The AOT12N60FD/AOB12N60FD/AOTF12N60FD have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.

By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

For Halogen Free add "L" suffix to part number:
AOT12N60FDL & AOB12N60FDL & AOTF12N60FDL

Product Summary

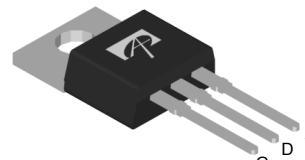
V_{DS}	700V@150°C
I_D (at $V_{GS}=10V$)	12A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 0.65Ω

100% UIS Tested
100% R_g Tested



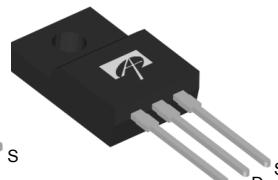
Top View

TO-220



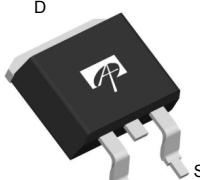
AOT12N60FD

TO-220F

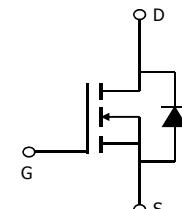


AOTF12N60FD

TO-263
D²PAK



AOB12N60FD



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	AOT12N60FD/AOB12N60FD		AOTF12N60FD	Units
Drain-Source Voltage	V_{DS}	600			V
Gate-Source Voltage	V_{GS}	± 30			V
Continuous Drain Current	I_D	$T_c=25^\circ C$	12	12*	A
$T_c=100^\circ C$			8	8*	
Pulsed Drain Current ^C	I_{DM}	48			
Avalanche Current ^C	I_{AR}	5			A
Repetitive avalanche energy ^C	E_{AR}	375			mJ
Single pulsed avalanche energy ^G	E_{AS}	750			mJ
Peak diode recovery dv/dt	dv/dt	5			V/ns
Power Dissipation ^B	P_D	$T_c=25^\circ C$	278	50	W
Derate above $25^\circ C$			2.2	0.4	W/ $^\circ C$
Junction and Storage Temperature Range	T_J , T_{STG}	-55 to 150			$^\circ C$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300			$^\circ C$
Thermal Characteristics					
Parameter	Symbol	AOT12N60FD/AOB12N60FD		AOTF12N60FD	Units
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JA}$	65		65	$^\circ C/W$
Maximum Case-to-sink ^A	$R_{\theta CS}$	0.5		--	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	0.45		2.5	$^\circ C/W$

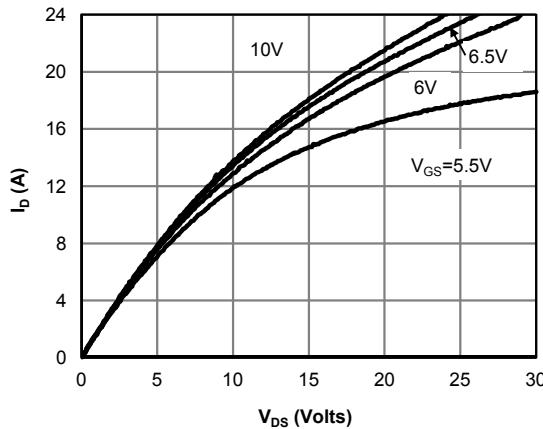
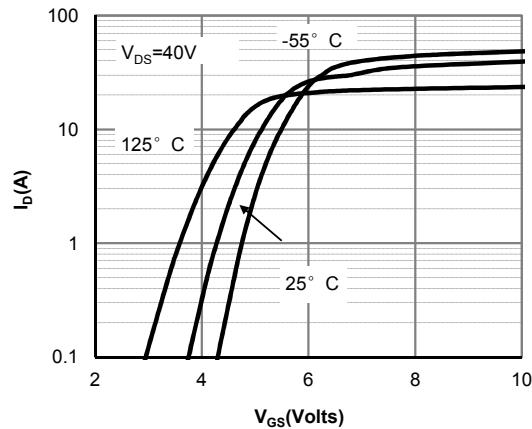
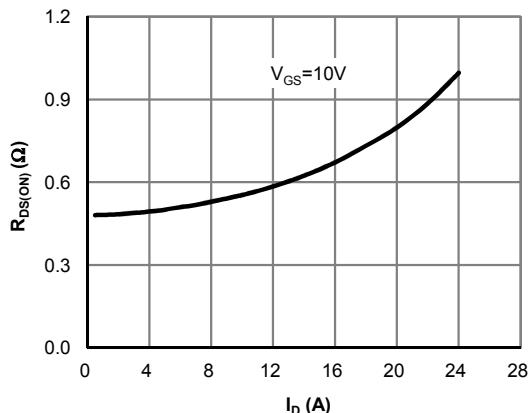
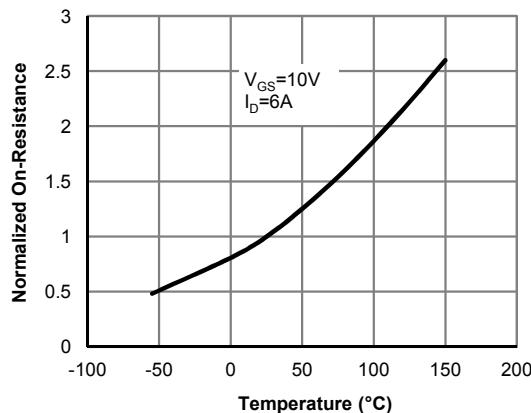
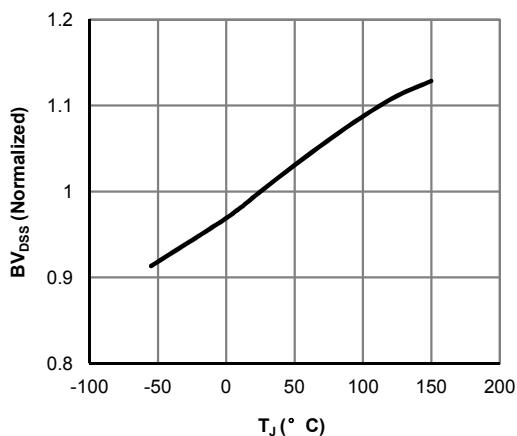
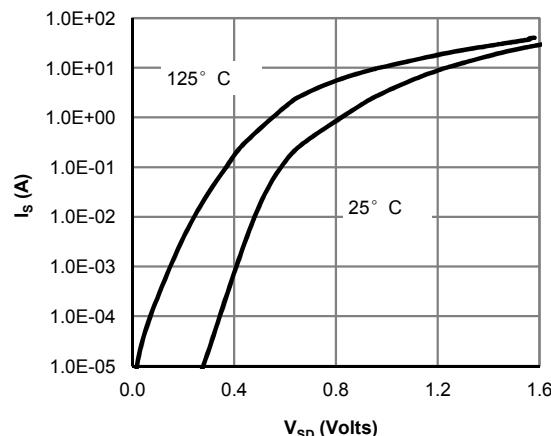
* Drain current limited by maximum junction temperature.

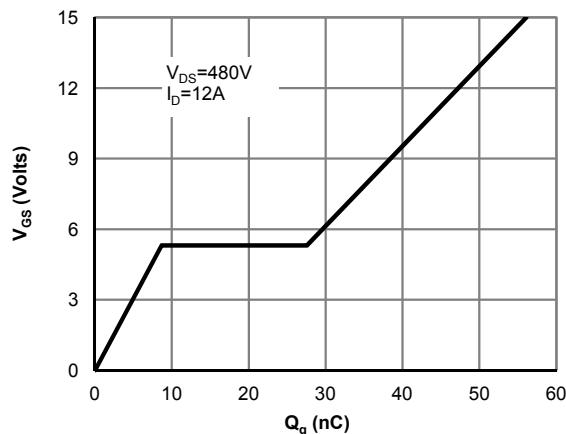
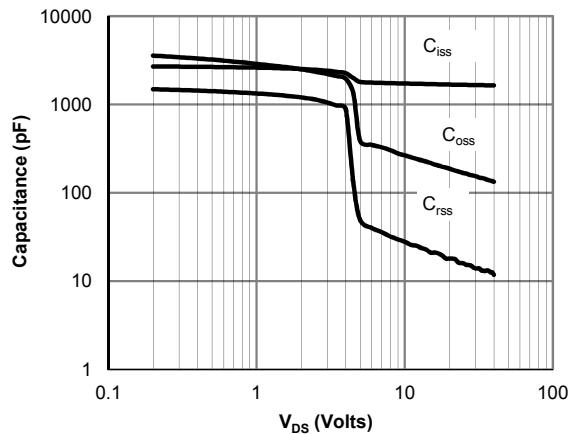
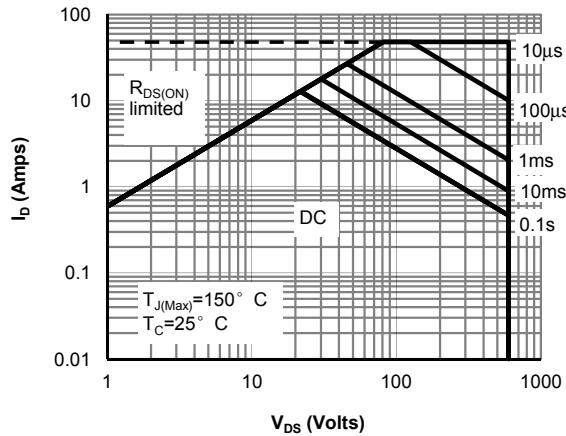
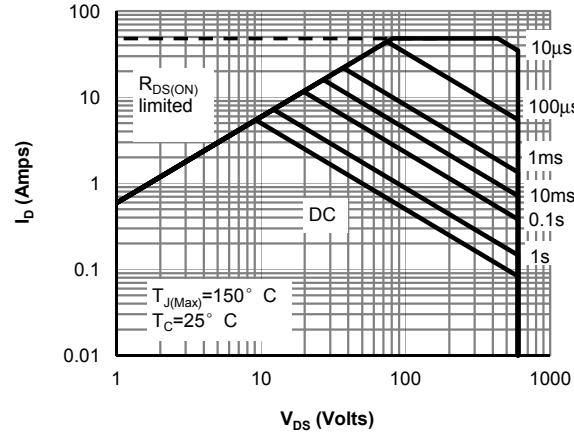
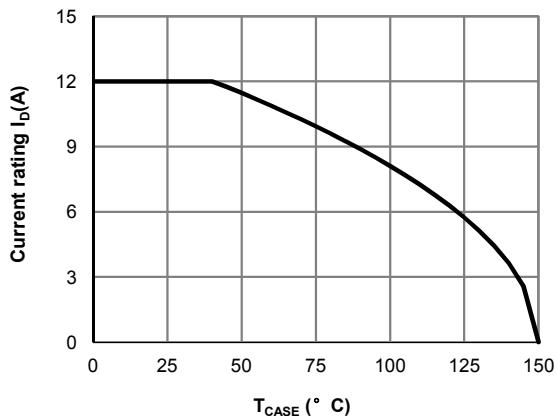
Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =10mA, V _{GS} =0V, T _J =25°C	600			V
		I _D =10mA, V _{GS} =0V, T _J =150°C		700		
BV _{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I _D =10mA, V _{GS} =0V		0.68		V/ $^\circ\text{C}$
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V			10	μA
		V _{DS} =480V, T _J =125°C			100	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±30V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V I _D =250 μA	2.4	3	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =6A		0.51	0.65	Ω
g _{Fs}	Forward Transconductance	V _{DS} =40V, I _D =6A		12		S
V _{SD}	Diode Forward Voltage	I _S =12A, V _{GS} =0V		1.3	1.6	V
I _S	Maximum Body-Diode Continuous Current				12	A
I _{SM}	Maximum Body-Diode Pulsed Current				48	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1MHz	1310	1659	2010	pF
C _{oss}	Output Capacitance		110	166	220	pF
C _{rss}	Reverse Transfer Capacitance		9	15.8	23	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.8	3.7	5.6	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =12A	32	41	50	nC
Q _{gs}	Gate Source Charge			8.7		nC
Q _{gd}	Gate Drain Charge			19		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =300V, I _D =12A, R _G =25 Ω		34		ns
t _r	Turn-On Rise Time			90		ns
t _{D(off)}	Turn-Off DelayTime			120		ns
t _f	Turn-Off Fall Time			82		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =12A, dI/dt=100A/ μs , V _{DS} =100V		135	220	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =12A, dI/dt=100A/ μs , V _{DS} =100V		0.5	0.8	μC

- A. The value of R_{BJA} is measured with the device in a still air environment with T_A=25° C.
 B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
 C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C, Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
 D. The R_{BJA} is the sum of the thermal impedance from junction to case R_{BJC} and case to ambient.
 E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.
 F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
 G. L=60mH, I_{AS}=5A, V_{DD}=150V, R_G=25 Ω , Starting T_J=25° C

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig 1: On-Region Characteristics

Figure 2: Transfer Characteristics

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature

Figure 5:Break Down vs. Junction Temperature

Figure 6: Body-Diode Characteristics(Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Area for AOT12N60FD/AOB12N60FD (Note F)

Figure 10: Maximum Forward Biased Safe Operating Area for AOTF12N60FD (Note F)

Figure 11: Current De-rating (Note B)

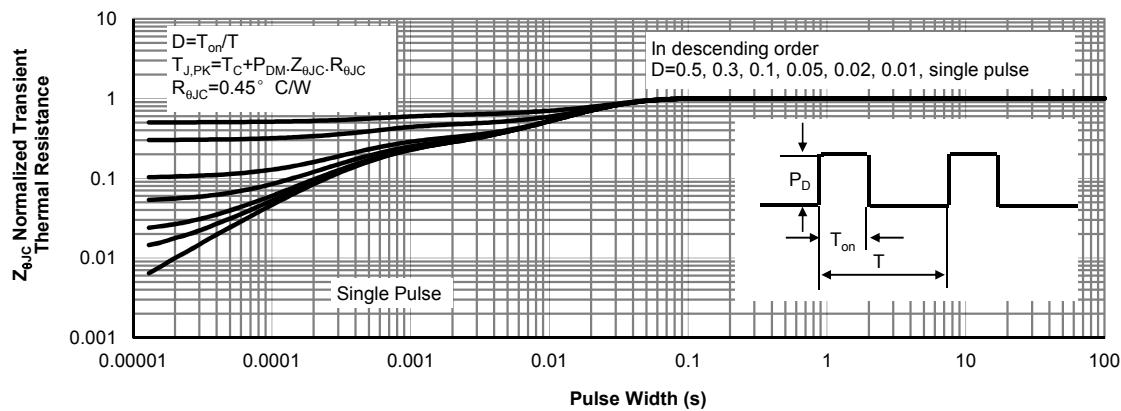
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Figure 12: Normalized Maximum Transient Thermal Impedance for AOT12N60FD/AOB12N60FD (Note F)

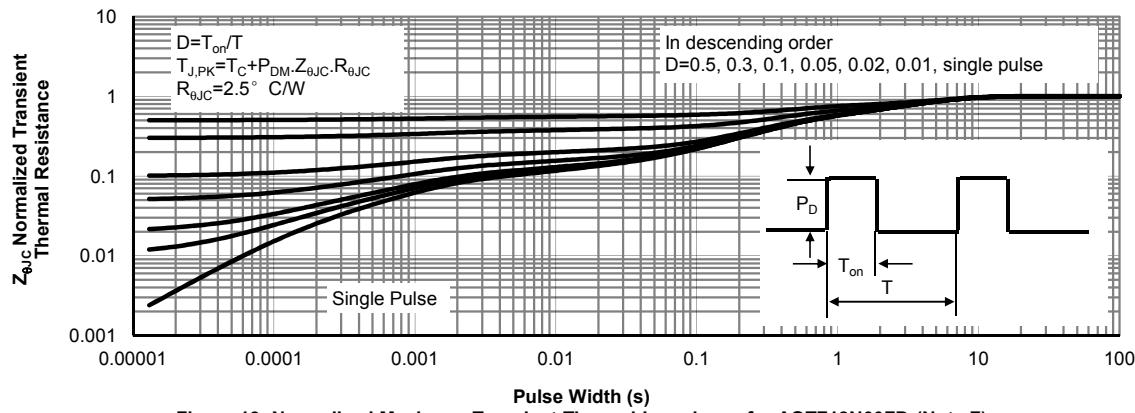


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF12N60FD (Note F)

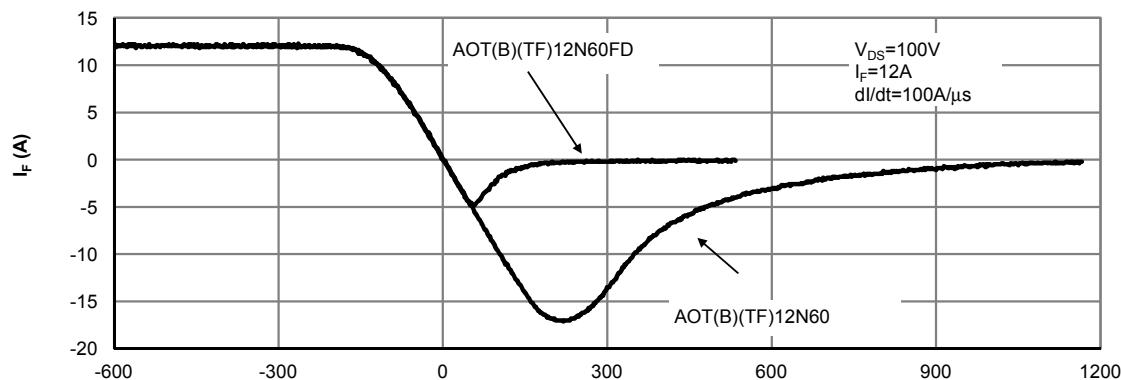
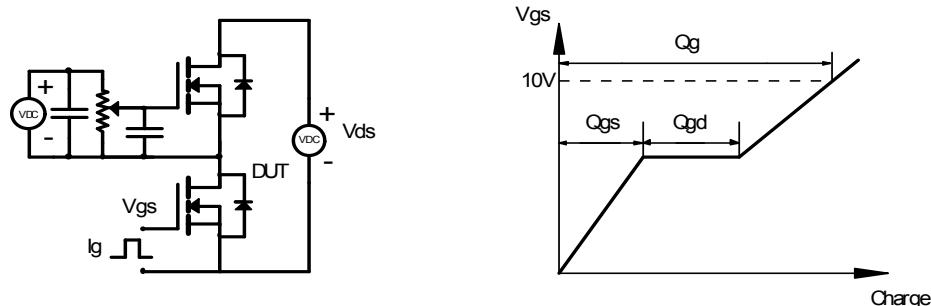
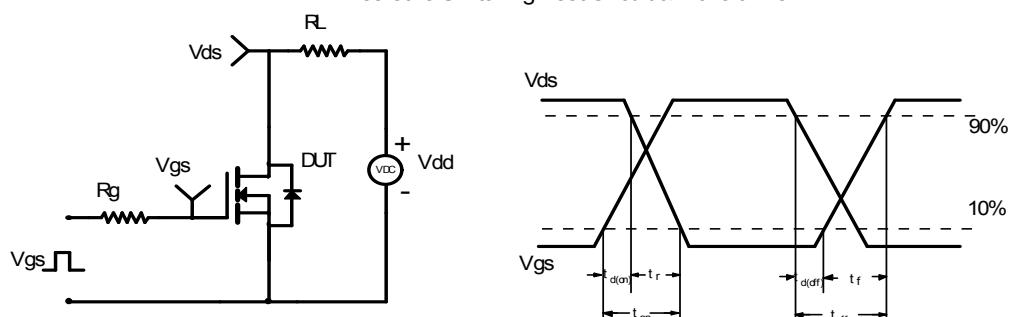


Figure 14: Diode Recovery Characteristics

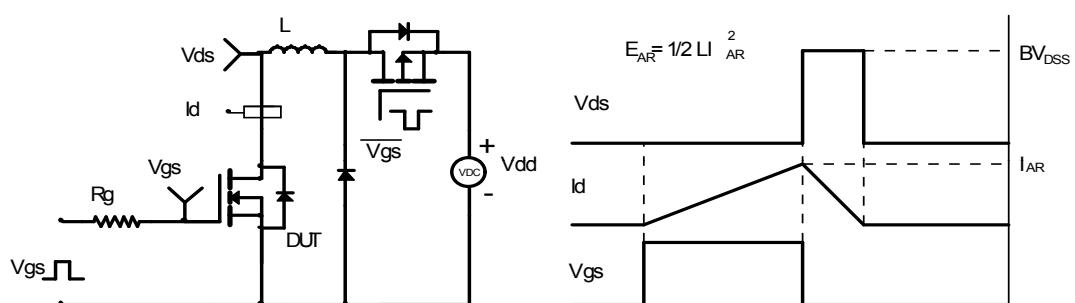
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

